

Notice of References Cited

Application/Control No.

10/567,729

Applicant(s)/Patent Under

Reexamination

KOJIMA ET AL.

Examiner

SARAH K. SALERNO

Art Unit

2814

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*	Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A US-6,165,874	12-2000	Powell et al.	438/478
	B US-			
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	L US-			
	M US-			

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NON-PATENT DOCUMENTS

*	Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
U	Steckl et al. ("Epitaxial Growth of B-SiC on Si by RTCVD with C3H8 and SiH4"; IEEE Transactions on Electron Devices Vol. 39, No. 1, Jan 1992 pages 64-73)
V	Hallin et al. "Homoepitaxial on-axis growth of 4H- and 6H-SiC by CVD" Materials Science Forum Vols. 457-460 (2004) pp. 193-196
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a))
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.